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10678766 - GAU: 1792 PTO/SB/08 Equivalent

	Application No.	10/678,766
INFORMATION DISCLOSURE	Filing Date	October 2, 2003
STATEMENT BY APPLICANT	First Named Inventor	Tois et al.
STATEMENT DI AFFLICANT	Art Unit	1792
(Multiple sheets used when necessary)	Examiner	Matthew J. Song
SHEET 1 OF 2	Attorney Docket No.	SEPP21.001C1

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Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
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	2	5,496,597	03-05-1996	Soininen et al.	
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	15	JP 03082769 A	04-1991	Tanaka, Naoto		Abstract
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Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
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Examiner S	Signature
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Date Considered

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Signature Date Considered 03/27/2010 /Matthew Song/

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